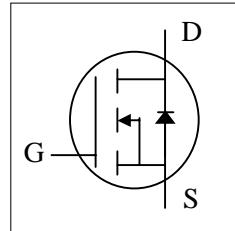
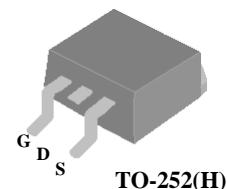




- ▼ Low On-resistance
- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant & Halogen-Free



BV_{DSS}	30V
$R_{DS(ON)}$	6.5mΩ
I_D	66A



Description

AP83T03A series are from Advanced Power innovative design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TO-252 package is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for high current application due to the low connection resistance.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	66	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	42	A
I_{DM}	Pulsed Drain Current ¹	160	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	50	W
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ³	2	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Units
R_{thj-c}	Maximum Thermal Resistance, Junction-case	2.5	°C/W
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient (PCB mount) ³	62.5	°C/W



AP83T03AGH-HF

Electrical Characteristics@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	30	-	-	V
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance ²	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=40\text{A}$	-	-	6.5	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=30\text{A}$	-	-	9.5	$\text{m}\Omega$
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1	-	3	V
g_{fs}	Forward Transconductance	$V_{\text{DS}}=10\text{V}, I_{\text{D}}=40\text{A}$	-	60	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{\text{DS}}=24\text{V}, V_{\text{GS}}=0\text{V}$	-	-	10	μA
I_{GSS}	Gate-Source Leakage	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Q_{g}	Total Gate Charge	$I_{\text{D}}=40\text{A}$	-	14	22.4	nC
Q_{gs}	Gate-Source Charge	$V_{\text{DS}}=24\text{V}$	-	3	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{\text{GS}}=4.5\text{V}$	-	8	-	nC
$t_{\text{d(on)}}$	Turn-on Delay Time	$V_{\text{DS}}=15\text{V}$	-	8	-	ns
t_{r}	Rise Time	$I_{\text{D}}=40\text{A}$	-	85	-	ns
$t_{\text{d(off)}}$	Turn-off Delay Time	$R_{\text{G}}=3.3\Omega$	-	22	-	ns
t_{f}	Fall Time	$V_{\text{GS}}=10\text{V}$	-	4.5	-	ns
C_{iss}	Input Capacitance	$V_{\text{GS}}=0\text{V}$	-	1080	1728	pF
C_{oss}	Output Capacitance	$V_{\text{DS}}=25\text{V}$	-	270	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	110	-	pF
R_{g}	Gate Resistance	$f=1.0\text{MHz}$	-	1.4	2.8	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_{\text{S}}=40\text{A}, V_{\text{GS}}=0\text{V}$	-	-	1.2	V
t_{rr}	Reverse Recovery Time	$I_{\text{S}}=10\text{A}, V_{\text{GS}}=0\text{V},$ $dI/dt=100\text{A}/\mu\text{s}$	-	21	-	ns
Q_{rr}	Reverse Recovery Charge		-	7	-	nC

Notes:

- 1.Pulse width limited by max. junction temperature
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

APEC RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.

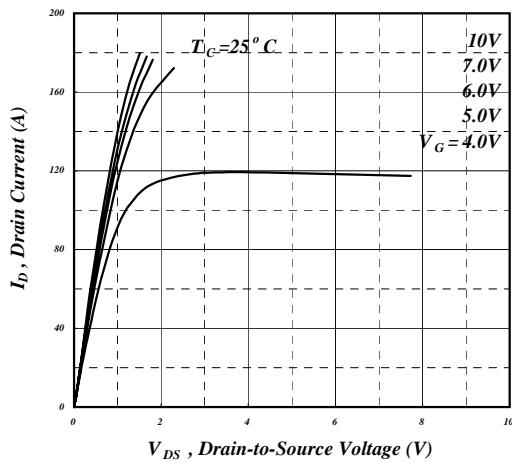


Fig 1. Typical Output Characteristics

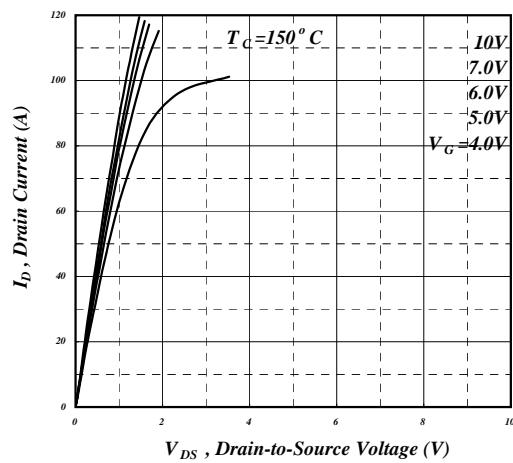


Fig 2. Typical Output Characteristics

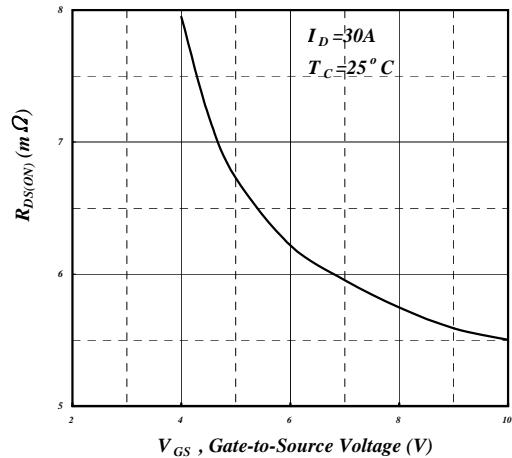


Fig 3. On-Resistance v.s. Gate Voltage

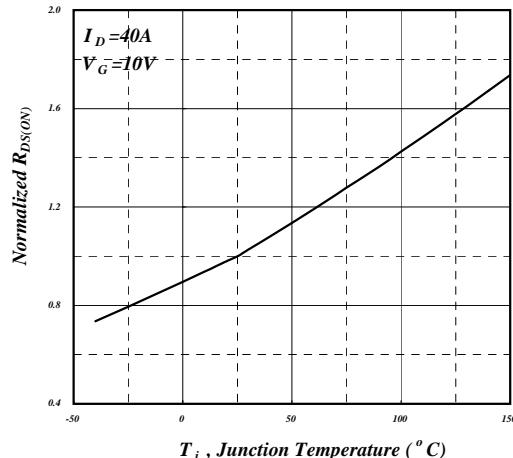


Fig 4. Normalized On-Resistance v.s. Junction Temperature

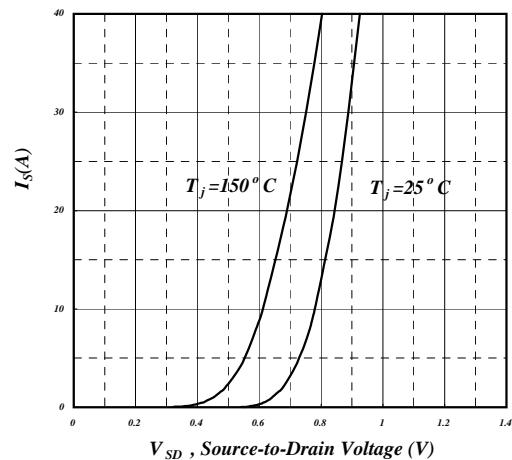


Fig 5. Forward Characteristic of Reverse Diode

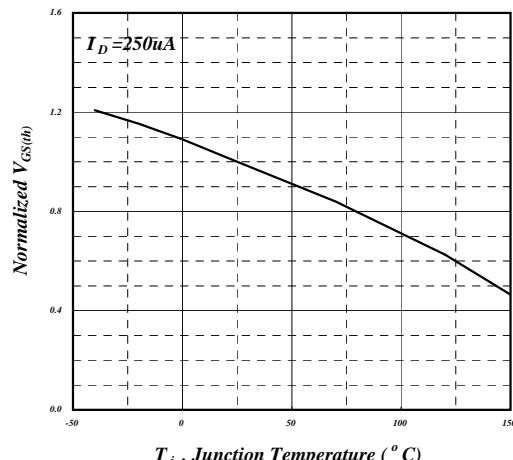


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

AP83T03AGH-HF

